

ABSTRACT OF THE DISCLOSURE

A method of fabricating a semiconductor device including: a first step of forming a through hole in a semiconductor element having electrodes on a first surface; and a second step of forming a conductive layer which is electrically connected to the electrodes and is provided from the first surface through an inner wall of the through hole to a second surface of the semiconductor element which is opposite to the first surface. The conductive layer is formed to have connecting portions on the first and second surfaces so that a distance between at least two electrodes among the electrodes is different from a distance between the connecting portions on at least one of the first and second surfaces, in the second step.